P-Channel NexFET™ Power MOSFET

Check for Samples: CSD23201W10

FEATURES

- **Ultra Low Qg and Qgd**
- **Small Footprint 1mm × 1mm**
- **Low Profile 0.62mm Height**
- **Pb Free**
- **Gate ESD Protection – 3kV**
- **RoHS Compliant**
- **Halogen Free**

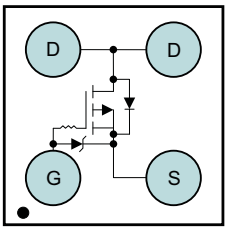
APPLICATIONS

- **Battery Management**
- **Load Switch**
- **Battery Protection**

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

Top View



PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	–12		V
Q_g	Gate Charge Total (4.5V)	1.8		nC
Q_{gd}	Gate Charge Gate to Drain	0.26		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = –1.5V	110	mΩ
		V_{GS} = –2.5V	77	mΩ
		V_{GS} = –4.5V	66	mΩ
$V_{GS(th)}$	Threshold Voltage	–0.6		V

ORDERING INFORMATION

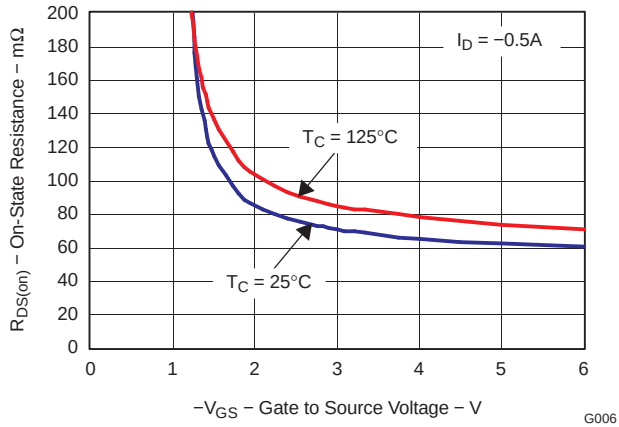
Device	Package	Media	Qty	Ship
CSD23201W10	1 × 1 Wafer Level Package	7-inch reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

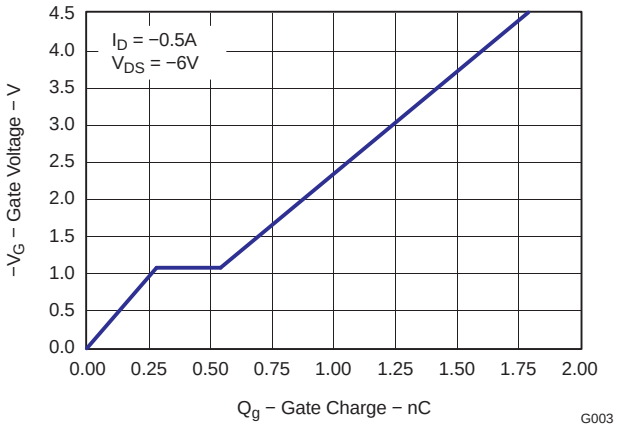
T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	–12	V
V_{GS}	Gate to Source Voltage	–6	V
I_D	Continuous Drain Current, T_C = 25°C(1)	–2.2	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	–8.8	A
I_G	Continuous Gate Clamp Current	–0.5	A
	Pulsed Gate Clamp Current	–7	A
P_D	Power Dissipation(1)	1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C

(1) $R_{\theta JA}$ = 100°C/W on 1in^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
(2) Pulse width ≤300μs, duty cycle ≤2%

$R_{DS(ON)}$ vs V_{GS}



Gate Charge



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = –250μA	–12			V
BV_{GSS}	Gate to Source Voltage;	V_{DS} = 0V, I_G = –250μA	–6.1		–7.2	V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = –9.6V			–1	μA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = –6V			–100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = –250μA	–0.4	–0.6	–1.0	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = –1.5V, I_D = –0.5A		110	138	mΩ
		V_{GS} = –2.5V, I_D = –0.5A		77	96	mΩ
		V_{GS} = –4.5V, I_D = –0.5A		66	82	mΩ
g_{fs}	Transconductance	V_{DS} = –6.0V, I_D = –0.5A		9		S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V, V_{DS} = –6.0V, f = 1MHz		250	325	pF
C_{OSS}	Output Capacitance			125	155	pF
C_{RSS}	Reverse Transfer Capacitance			32	42	pF
Q_g	Gate Charge Total (–4.5V)	V_{DS} = –6.0V, I_D = –0.5A		1.8	2.4	nC
Q_{gd}	Gate Charge Gate to Drain			0.26		nC
Q_{gs}	Gate Charge Gate to Source			0.28		nC
$Q_{g(th)}$	Gate Charge at Vth			0.11		nC
Q_{OSS}	Output Charge	V_{DS} = –6.0V, V_{GS} = 0V		1.7		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = –6.0V, V_{GS} = –2.5V, I_D = –0.5A, R_G = 20Ω		24		ns
t_r	Rise Time			19		ns
$t_{d(off)}$	Turn Off Delay Time			68		ns
t_f	Fall Time			29		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_S = –0.5A, V_{GS} = 0V		–0.77	–1.0	V
Q_{rr}	Reverse Recovery Charge	V_{dd}= –4.0V, I_F = –0.5A, di/dt = 100A/μs		2		nC
t_{rr}	Reverse Recovery Time	V_{dd}= –4.0V, I_F = –0.5A, di/dt = 100A/μs		9.5		ns

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Ambient (Minimum Cu area)			245	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1 in^2 Cu area)			125	°C/W

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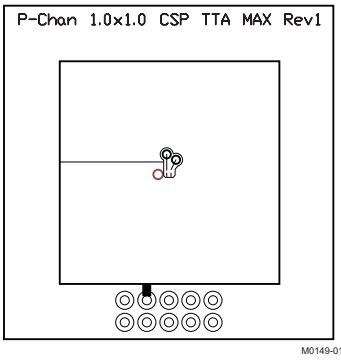
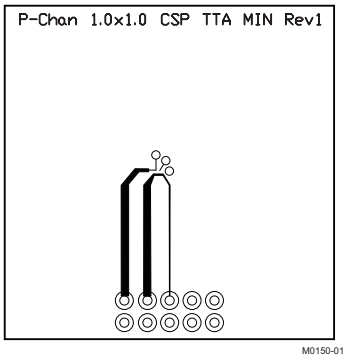


Max $R_{\theta JA}$ = 125°C/W when mounted on 1inch^2 of 2 oz. Cu.



Max $R_{\theta JA}$ = 245°C/W when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

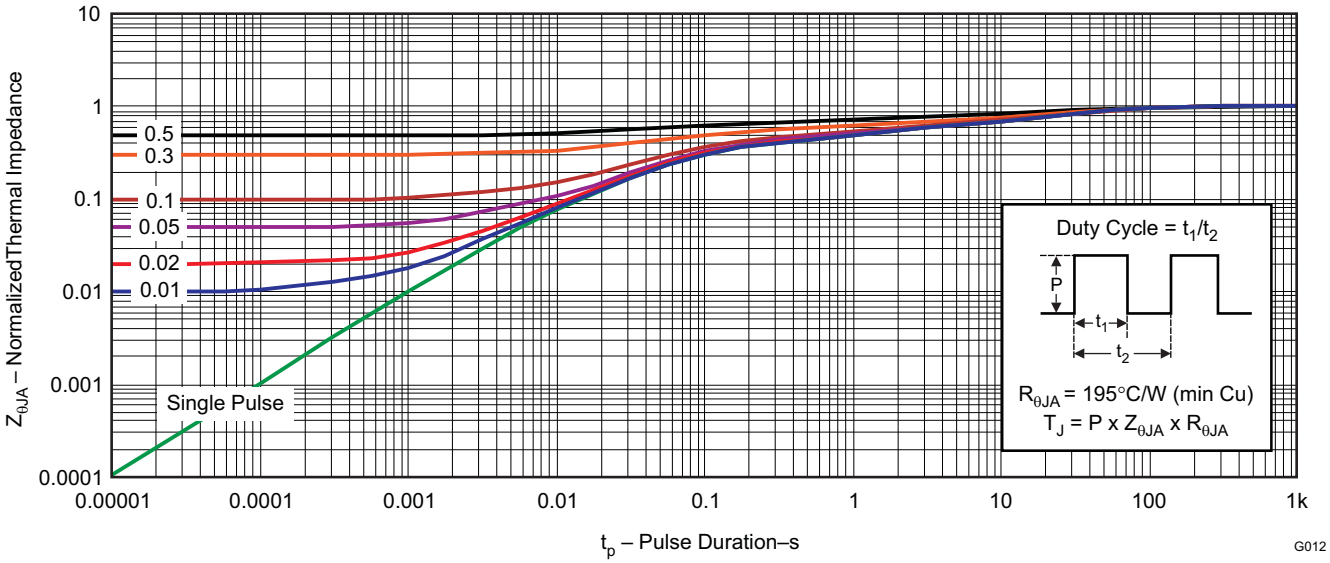


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

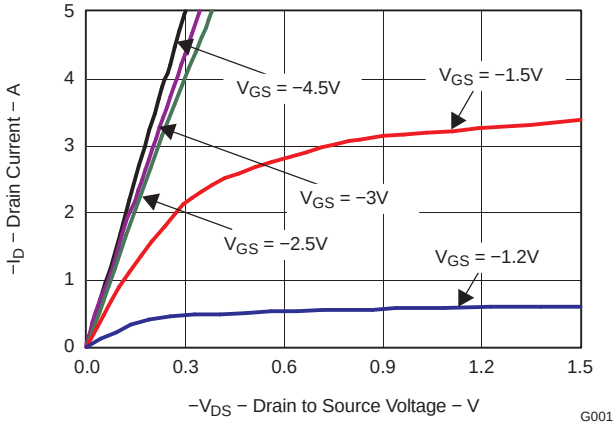


Figure 2. Saturation Characteristics

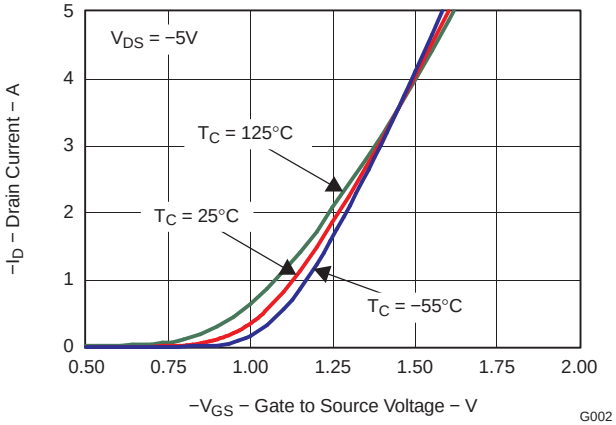


Figure 3. Transfer Characteristics

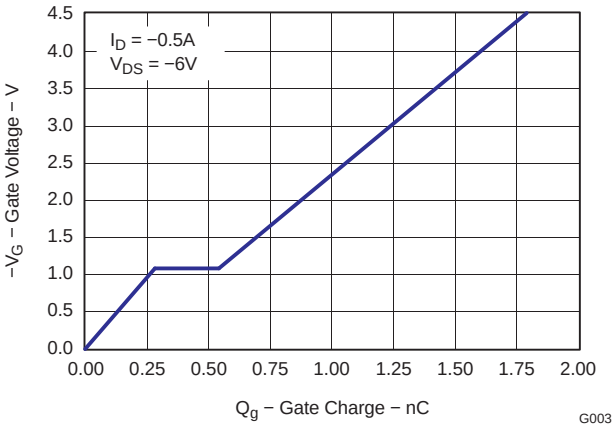


Figure 4. Gate Charge

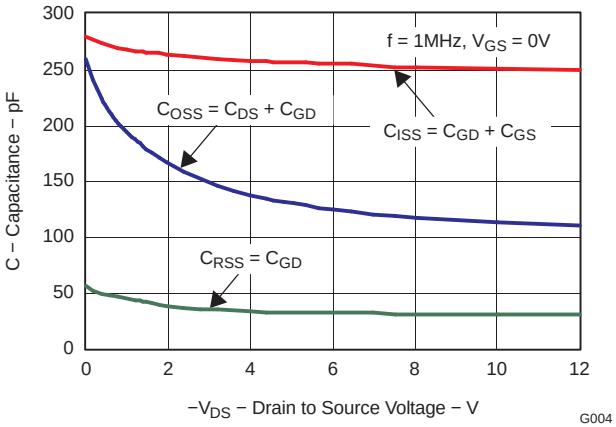


Figure 5. Capacitance

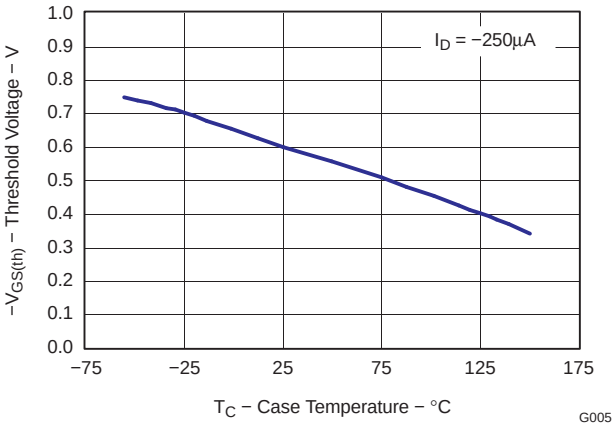


Figure 6. Threshold Voltage vs. Temperature

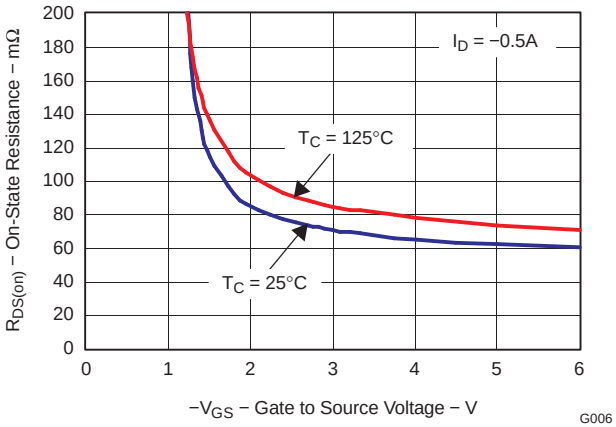


Figure 7. On Resistance vs. Gate Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

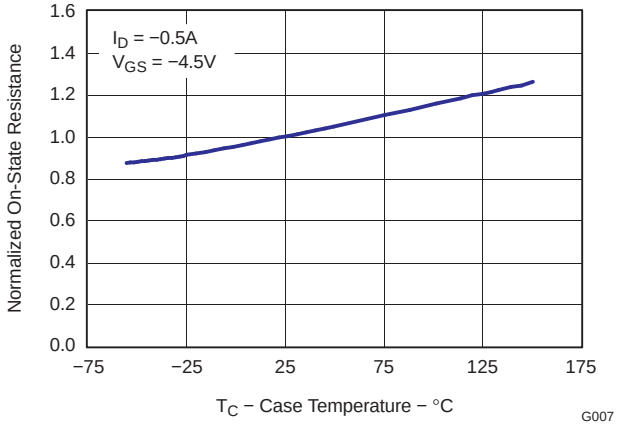


Figure 8. On Resistance vs. Temperature

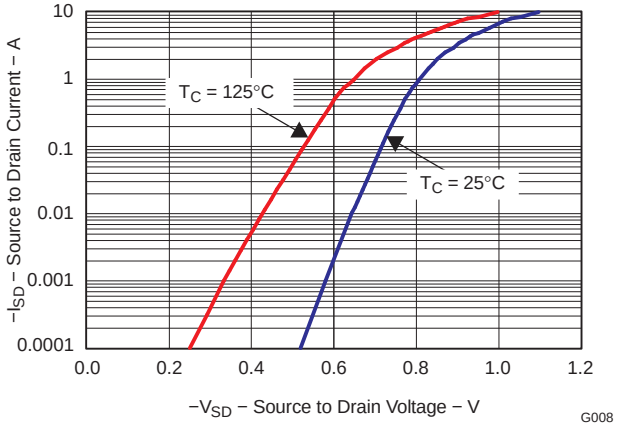


Figure 9. Typical Diode Forward Voltage

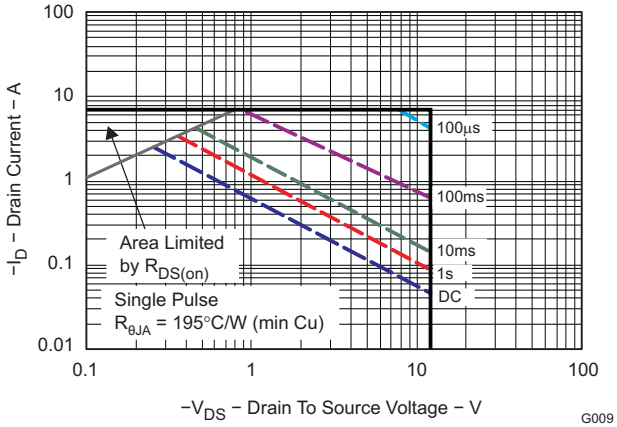


Figure 10. Maximum Safe Operating Area

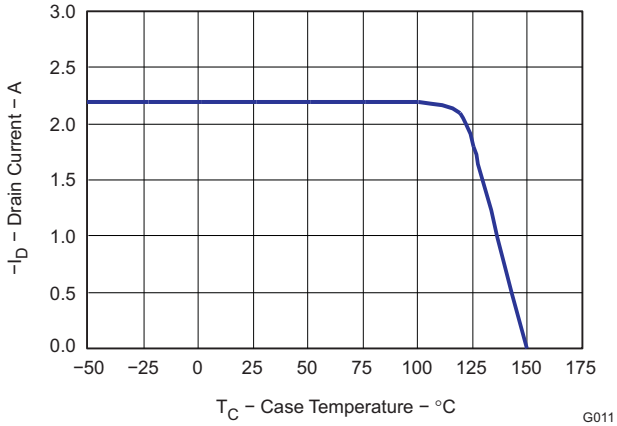
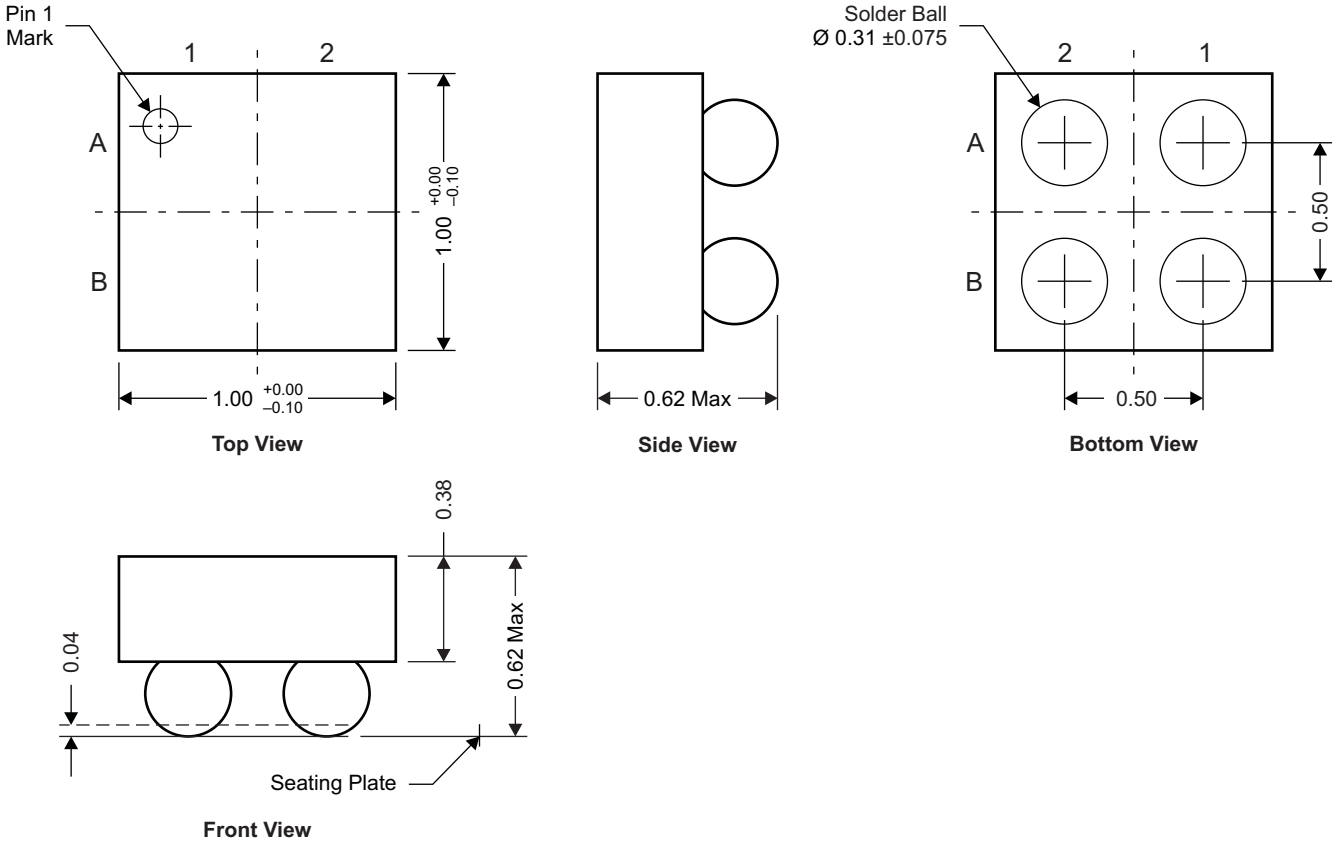


Figure 11. Maximum Drain Current vs. Temperature

MECHANICAL DATA

CSD23201W10 Package Dimensions



NOTE: All dimensions are in mm (unless otherwise specified)

Pin Configuration Table

POSITION	DESIGNATION
B1	Source
A1	Gate
A2, B2	Drain

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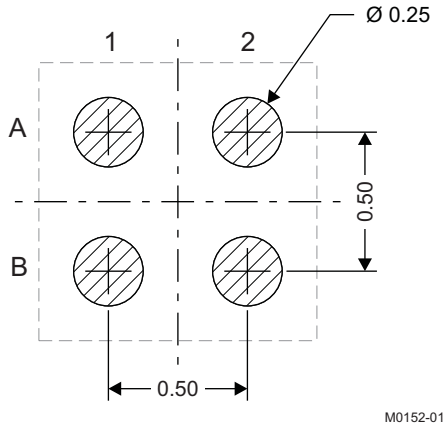
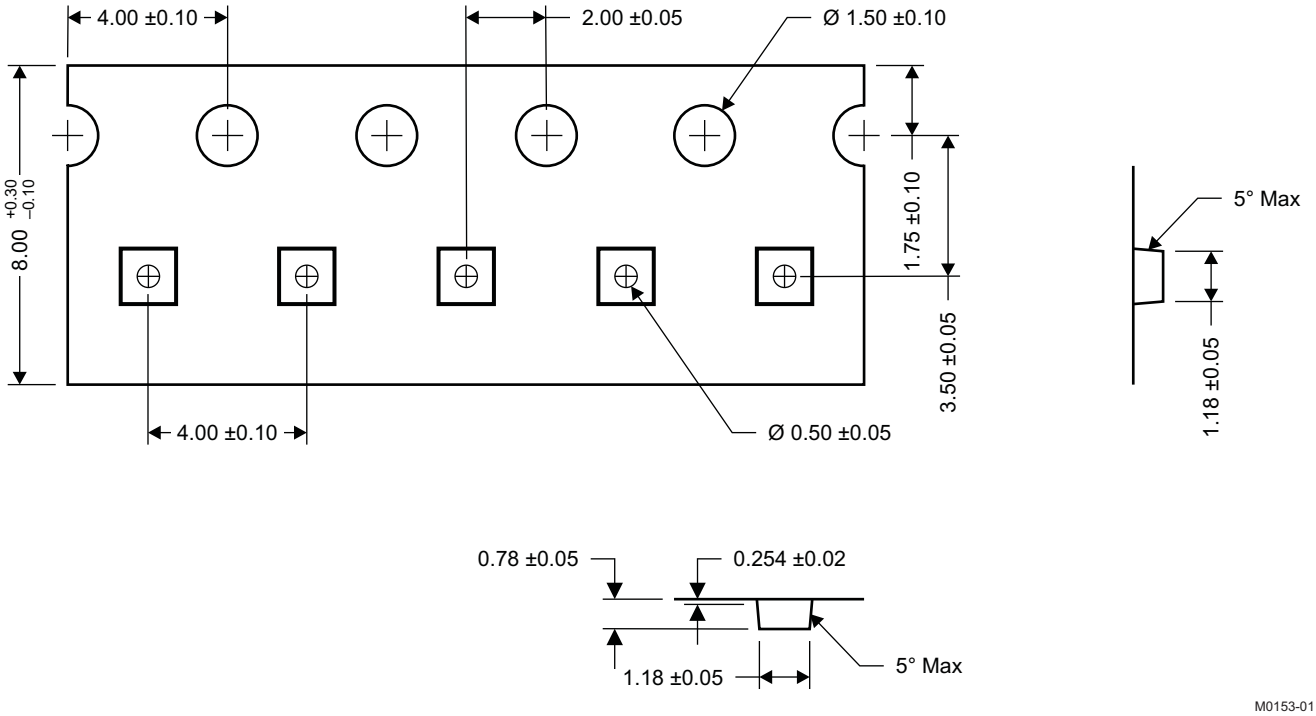
Land Pattern Recommendation



NOTE: All dimensions are in mm (unless otherwise specified)

Tape and Reel Information



NOTE: All dimensions are in mm (unless otherwise specified)

REVISION HISTORY

Changes from Original (August 2009) to Revision A	Page
• Deleted the Package Marking Information section	7

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